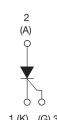


## VS-25TTS...PbF Series, VS-25TTS...-M3 Series

Vishay Semiconductors

## **High Voltage Phase Control Thyristor, 25 A**





TO	-22	0AB

PRODUCT SUMMARY					
Package	TO-220AB				
Diode variation	Single SCR				
I <sub>T(AV)</sub>	16 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V				
V <sub>TM</sub>	1.25 V				
I <sub>GT</sub>	45 mA				
TJ	- 40 °C to 125 °C				

#### **FEATURES**

 Designed and qualified according JEDEC-JESD47



• 125 °C max. operating junction temperature

• Compliant to RoHS Directive 2002/95/EC

 Halogen-free according to IEC 61249-2-21 COMPLIANT definition (-M3 only) **HALOGEN** FREE

## RoHS

#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

#### **DESCRIPTION**

The VS-25TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	18	22	А		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>T(AV)</sub>	Sinusoidal waveform	16	٨		
I <sub>RMS</sub>		25	A		
V <sub>RRM</sub> /V <sub>DRM</sub>		800/1200	V		
I <sub>TSM</sub>		300	Α		
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V		
dV/dt		500	V/µs		
dl/dt		150	A/μs		
T <sub>J</sub>		- 40 to 125	°C		

VOLTAGE RATINGS					
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA		
VS-25TTS08PbF, VS-25TTS08-M3	800	800	10		
VS-25TTS12PbF, VS-25TTS12-M3	1200	1200	10		



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
PARAMETER	SYMBOL	IESI CO	ВИППОМ	TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° conduc	ction half sine wave	1	6	
Maximum RMS on-state current	I <sub>RMS</sub>			2	5	Α
Maximum peak, one-cycle,	-	10 ms sine pulse, rated	V <sub>RRM</sub> applied	30	00	_ ^
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no volt	tage reapplied	3	50	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated	V <sub>RRM</sub> applied	4	50	A <sup>2</sup> s
wiaximum i-t for fusing	I <del>-</del> t	10 ms sine pulse, no voltage reapplied		63	30	A-5
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 to 10 ms, no voltage reapplied		63	00	A²√s
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C		1.3	25	V
On-state slope resistance	r <sub>t</sub>	− T <sub>.l</sub> = 125 °C		12	2.0	mΩ
Threshold voltage	V <sub>T(TO)</sub>	1j = 125 C		1	.0	V
Maximum reverse and direct leakage current	1/1	T <sub>J</sub> = 25 °C	V Potod V/V	0	.5	
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	$V_R = Rated V_{RRM}/V_{DRM}$		1	0	mA
Holding current	l <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T = 1 \text{ A}$		-	100	IIIA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load		20	00	
Maximum rate of rise of off-state voltage	dV/dt			50	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			150		A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	$P_{GM}$		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60	mA	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5		
Maximum required DC gate voltage to trigger	$V_{\mathrm{GT}}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	V	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value 0.25 2.0			
Maximum DC gate current not to trigger	I <sub>GD</sub>			mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9		
Typical reverse recovery time	t <sub>rr</sub>	T, <sub>I</sub> = 125 °C	4	μs	
Typical turn-off time	tq	1 1 1 2 5 6	110		

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		$T_J$ , $T_{Stg}$		- 40 to 125	°C	
Maximum thermal resistance, junction to case		$R_{thJC}$	DC operation	1.1		
Maximum thermal resistance, junction to ambient		$R_{thJA}$		62	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	OZ.	
Mounting torque ————	minimum			6 (5)	kgf · cm	
	maximum			12 (10)	(lbf ⋅ in)	
Madianalasia			Occasional TO COOMP	25TTS08		
Marking device			Case style TO-220AB		25TTS12	

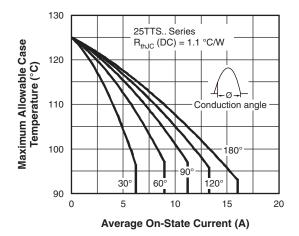


Fig. 1 - Current Rating Characteristics

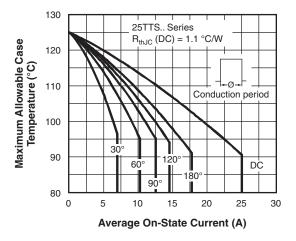


Fig. 2 - Current Rating Characteristics

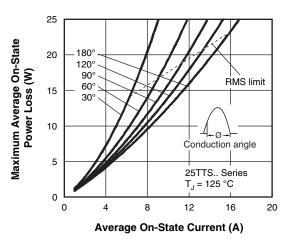


Fig. 3 - On-State Power Loss Characteristics

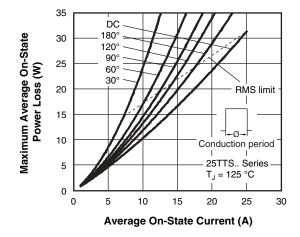


Fig. 4 - On-State Power Loss Characteristics

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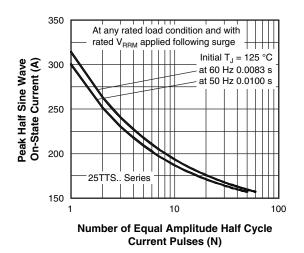


Fig. 5 - Maximum Non-Repetitive Surge Current

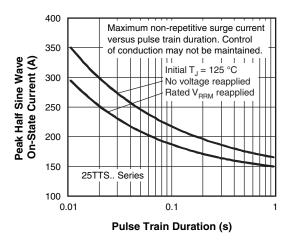


Fig. 6 - Maximum Non-Repetitive Surge Current

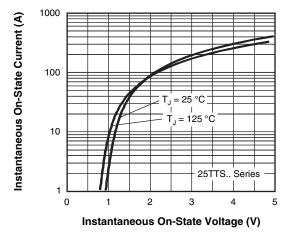


Fig. 7 - On-State Voltage Drop Characteristics

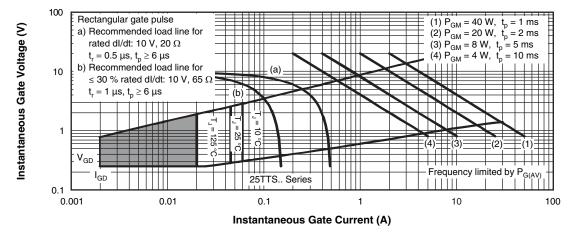


Fig. 8 - Gate Characteristics

## VS-25TTS...PbF Series, VS-25TTS...-M3 Series

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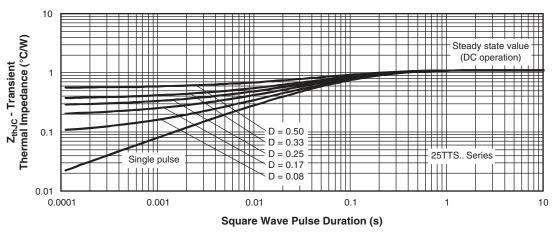
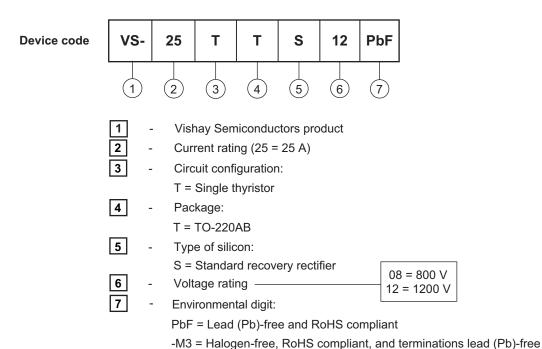


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

### **ORDERING INFORMATION TABLE**



ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-25TTS08PbF	50	1000	Antistatic plastic tubes		
VS-25TTS08-M3	50	1000	Antistatic plastic tubes		
VS-25TTS12PbF	50	1000	Antistatic plastic tubes		
VS-25TTS12-M3	50	1000	Antistatic plastic tubes		

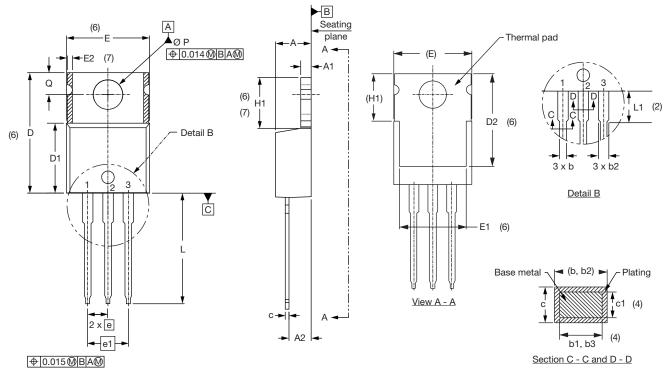
LINKS TO RELATED DOCUMENTS				
Dimensions		www.vishay.com/doc?95222		
Part marking information	TO-220AB PbF	www.vishay.com/doc?95225		
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028		



## Vishay Semiconductors

## **TO-220AB**

#### **DIMENSIONS** in millimeters and inches



# Lead tip

#### Lead assignments

#### **Diodes**

- 1. Anode/open
- 2. Cathode
- 3. Anode

#### Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Notes					

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		
		•		•	

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- Controlling dimensions: inches
- Thermal pad contour optional within dimensions E, H1, D2 and
- Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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